

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of:

Kaori TAI

Application No. New U.S. Patent Application

Filed: August 16, 2000

Attorney Dkt. 32011-165642

For: METHOD OF PRODUCING SEMICONDUCTOR DEVICES AND ETCHING  
LIQUIDS

**INFORMATION DISCLOSURE STATEMENT**

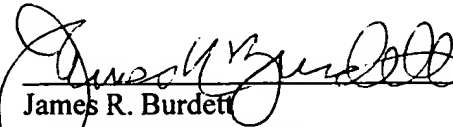
Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449 and/or listed herein. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date or the date of filing a new application OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.

Respectfully submitted,

  
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Date: August 16, 2000

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce <b>PATENT &amp; TRADEMARK OFFICE</b>		ATTY DOCKET NO. 32011-165642		APPLICATION NO. New Application	
<b>INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)				APPLICANT(S) Kaori TAI			
				FILING DATE August 16, 2000			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
		Goto et al., "Leakage Mechanism and Optimized Conditions of Co Salicide Process for Deep-Submicron CMOS Devices" IEDM Tech., Dig. 1995 IEEE, pp. 449.					
<b>EXAMINER</b>					<b>DATE CONSIDERED</b>		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							